



(Use several sheets if necessary)

PTO Form 1449

60999-185

10/783,830

Krutko et al.

February 20, 2004

2811

U.S. PATENT DOCUMENTS

[illegible]

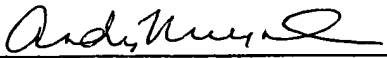
FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

ah	C01	W.J. Ho, M.F. Chang, S.M. Beccue, P.J. Zampardi, J. Yu, A. Sailer, R.L. Pierson, K.C. Wang, "A GaAs BiFET LSI technology", GaAs IC Sym. Tech. Dig., 1994, p.47.
ah	C02	D. Cheskis, C. E. Chang, W. H. Ku, P. M. Asbeck, M.F. Chang, R.L. Pierson, S. Sailer, "Co-integration of GaAlAs/GaAs HBT's and GaAs FET's with a simple manufacturable process", IEDM Tech. Dig., 1992, p. 91.
ah	C03	D. C. Streit, D. K. Umemoto, K. W. Kobayashi, A. K. Oki, "Monolithik HEMT-HBT integration by selective MBE". IEEE Trans. Electron Devices, vol. 42, 1995, p.618.
ah	C04	D. C. Streit, D. K. Umemoto, J. R. Velebir, K. W. Kobayashi, A. K. Oki, "35 GHz HEMT amplifiers fabricated using integration HEMT-HBT material grown by selective MBE", IEEE Microwave Guided Wave Lett., vol. 4, 1994, p.361.
ah	C05	K. Itakura, Y. Shimamoto, T. Ueda, S. Katsu, D. Ueda, " A GaAs Bi-FET technology for large scale integration", IEDM Tech. Dig., 1989, p. 389.

ah	C06	Y. F. Yang, C.C. Hsu, E.S. Yang, "Integration of GaInP/GaAs heterojunction bipolar transistors and high electron mobility transistors", IEEE Electron Device Lett., vol. 17, no. 7, July 1996, p. 363
ah	C07	J. H. Tsai, " Integrated fabrication of InGaP/GaAs d-doped heterojunction bipolar transistor and doped-channel field effect transistor", 2002 IEEE, p. 365.
ah	C08	J. Jang, E. C. Kan, T. Arnborg, T. Johansson, R. Dutton, "Characterization of RF Power BJT and Improvement of Thermal Stability with Nonlinear Base Ballasting", 1998 IEE, pg. 1428.

Examiner.		Date Considered	07/19/05
Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			